(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
15 April 2004 (15.04.2004)

PCT

(10) International Publication Number
WO 2004/030612 A2

(51) International Patent Classification[7]: A61K

(21) International Application Number:
PCT/US2003/027547

(22) International Filing Date:
3 September 2003 (03.09.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0210868 3 September 2002 (03.09.2002) FR

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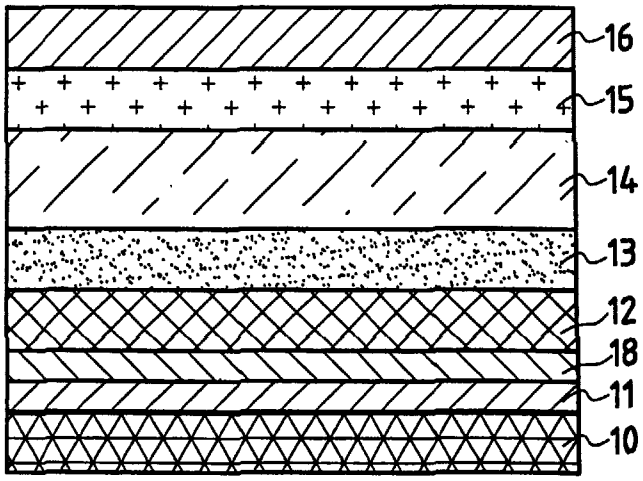
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, SE, SI, SK, TR).

Published:
— *without international search report and to be republished upon receipt of that report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: LIGHT EMITTING DIODE, SUPPORT & METHOD OF MANUFACTURE



(57) Abstract: A light emitting diode of the stacked-layer structure type, incorporating at least one layer made of an inorganic material between the layer forming the substrate and a layer forming the light emitting layer, is provided, in which a periodic structure at the wavelength range emitted by the light emitting layer is printed. Also described is a method for generating a microstructure periodic with a wavelength range of the emitting layer ofa light emitting diode. The method includes: depositing an inorganic material layer by a sol-gel process between the substrate and a light emitting layer, and printing the periodic structure onto the outer surface of this layer by soft lithography, as well as using this process for manufacturing a light emitting diode.

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